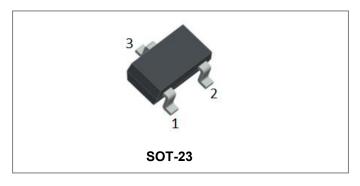






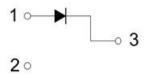
#### MMBD4150 SCHOTTKY BARRIER DIODE



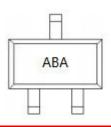
#### **Features**

- Surface mount device
- Double diodes with different pining are available
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



#### **Marking Diagram**



## Maximum Ratings@TA=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	50	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @Tc=25°C, rectangular wave form	0.25	А
Peak One Cycle Non-Repetitive Surge Current (per leg)	IFSM	1 us, half Sine pulse	4	Α
Power dissipation#	P <sub>tot</sub>	T <sub>amb</sub> = 25 °C	350	mW

# Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*		@ 1mA, Pulse, T <sub>J</sub> = 25 °C	0.45	0.62	
		@ 10mA, Pulse, T <sub>J</sub> = 25 °C	0.61	0.74	
	$V_{F1}$	@ 50mA, Pulse, T <sub>J</sub> = 25 °C	0.75	0.86	V
		@ 100mA, Pulse, T <sub>J</sub> = 25 °C	0.82	0.92	
		@ 200mA, Pulse, T <sub>J</sub> = 25 °C	0.90	1.0	
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R, \text{ Pulse, } T_J = 25  ^{\circ}\text{C}$	0.002	0.1	μA
Junction Capacitance	Ст	@V <sub>R</sub> = 0 V, Tc=25℃, fSIG = 1MHz	2.2	4	рF
Reverse Recovery Time	t <sub>rr</sub>	$I_F$ =10mA $I_R$ = 10mA $I_{rr}$ =1 mA $R_L$ =100 $\Omega$ $T_J$ = 25 °C	-	4	ns

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
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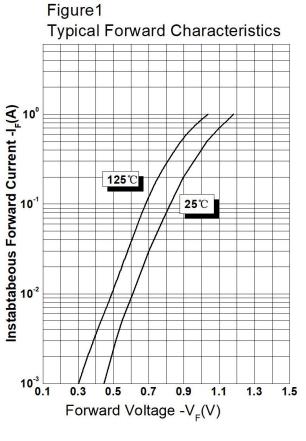


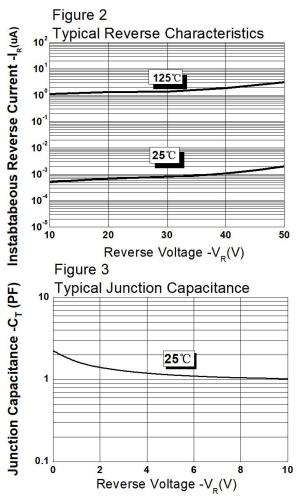


# Thermal-Mechanical Specifications

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-65 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-65 to +150	°C
Typical Thermal Resistance Junction to Ambient	R₀JA	DC operation	357	°C/W

### **Ratings and Characteristics Curves**





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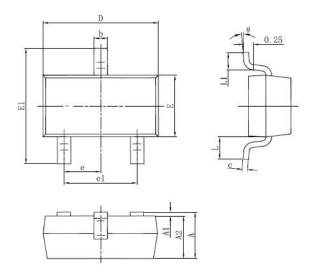


## **Ordering Information**

Device	Package	Shipping
MMBD4150	SOT-23(Pb-Free)	3000pcs / reel

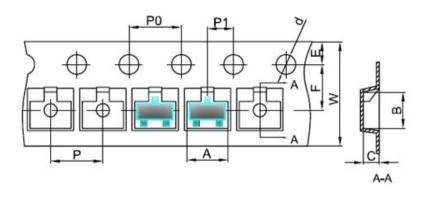
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

#### **Mechanical Dimensions SOT-23**



CVMDOL	Millimeters		Inches		
SYMBOL	MIN.	MAX.	MIN.	MAX.	
Α	0.890	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.076	0.170	0.003	0.007	
D	2.650	3.050	0.104	0.120	
E	1.190	1.400	0.047	0.055	
E1	2.100	2.550	0.083	0.100	
е	0.950 TYP.		0.037 TYP.		
e1	1.780	2.050	0.070	0.081	
Ĺ	0.550 REF.		0.022 REF.		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## **Carrier Tape Specification SOT-23**



SYMBOL	Millimeters			
	Min.	Max.		
Α	3.05	3.25		
В	2.67	2.87		
С	1.12	1.32		
d	1.40	1.60		
Е	1.65	1.85		
F	3.40	3.60		
Р	3.90	4.10		
P0	3.90	4.10		
P1	1.90	2.10		
W	7.90	8.30		

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